200V N-Channel Enhancement Mode MOSFET

1.Product Information

1.1 Features

- ◇ Surface-mounted package
- ◇ Advanced SGT cell design

1.2 Applications

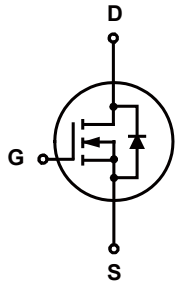
- ◇ BMS
- ◇ Drones
- ◇ High power inverter system
- ◇ Light electric vehicles

1.3 Quick reference

- ◇ BV ≧ 200 V
- ◇ P_{tot} ≦ 312 W
- ◇ I_D ≦ 75 A
- ◇ $R_{DS(ON)}$ ≦ 23 mΩ @ V_{GS} = 10 V

2.Pin Description

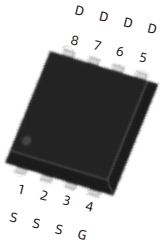
Symbol



Simplified Outline

Top View

PDFN5*6-8L



3.Marking Information

Product Name	Marking
LN190N200G-H	LN190N200G-H CYWWZZ XXXXXX

4.Limiting Values

Symbol	Parameter		Rating	Unit
V_{DS}	Drain-Source Voltage		200	V
V_{GS}	Gate-Source Voltage		± 20	V
I_D	Drain Current	T_C = 25 ℃	75	A
		T_C = 100 ℃	53	A
I_{DM} Note2	Pulsed Source Current	T_C = 25 ℃	150	A
I_S	Diode Forward Current	T_C = 25 ℃	75	A
E_{AS}	Single Pulsed Avalanche Energy	L= 1.0mH	612	mJ
P_{tot}	Total Power Dissipation	T_C = 25 ℃	312	W
$R_{\theta JA}$ Note1	Thermal Resistance- Junction to Ambient		58	℃ / W
$R_{\theta JC}$	Thermal Resistance- Junction to Case		0.5	℃ / W
T_{stg}	Storage Temperature		-55~175	℃
T_J	Junction Temperature		175	℃

Note1： Surface Mounted on 1 in² pad area, t ≤10 sec.
Note2： Pulse test;Pulse width ≤ 300 μs, duty cycle ≤ 2%.
Note3： Limited by bonding wire.

5.Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
LN190N200G-H	PDFN5*6-8L	Ø330mm	12mm	5000	

Note: COMTECH defines " Green " as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight;Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C)

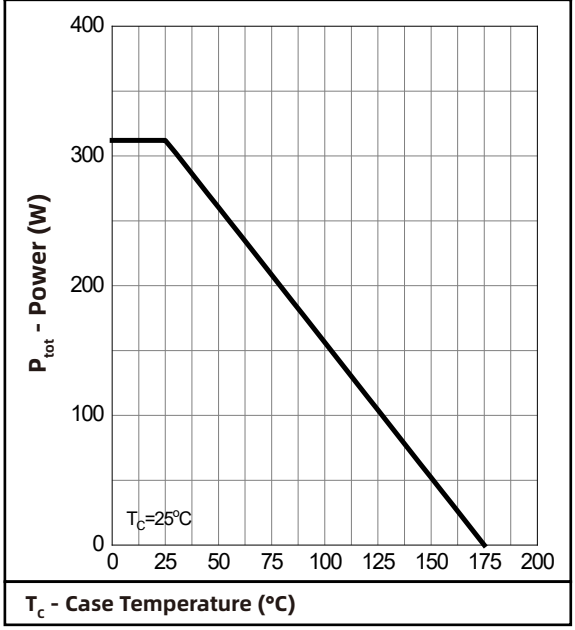
6. Electrical Characteristics (T_A=25 ° Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_{DS} = 250 μA	200	-	-	V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = 0 V, I_{DS} = 250 μA	3	-	5	V
I_{DSS}	Drain Leakage Current	V_{DS} = 160 V, V_{GS} = 0 V	-	-	1	μA
I_{GSS}	Gate Leakage Current	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	±100	nA
$R_{DS(ON)}$ Note1	On-State Resistance	V_{GS} = 10 V, I_{DS} = 30 A	-	19	23	mΩ
Diode Characteristics						
V_{SD} a	Diode Forward Voltage	I_{SD} = 30 A, V_{GS} = 0 V	-	-	1.3	V
t_{rr}	Reverse Recovery Time	I_{DS} = 30 A, V_{GS} = 0 V	-	103	-	nS
Q_{rr}	Reverse Recovery Charge	dI_{SD}/dt = 100 A/μs	-	470	-	nC
Dynamic Characteristics[b]						
C_{iSS}	Input Capacitance	V_{GS} = 0 V, V_{DS} = 100 V Frequency = 1 MHz	-	1838	-	pF
C_{OSS}	Output Capacitance		-	191	-	
C_{rSS}	Reverse Transfer Capacitance		-	54	-	
t_d(on)	Turn-on Delay Time	V_{DS} = 100 V, V_{GEN} = 10 V, R_G = 3.9 Ω, R_L = 3.3 Ω, I_{DS} = 30 A	-	13	-	nS
t_r	Turn-on Rise Time		-	42	-	
t_d(off)	Turn-off Delay Time		-	19	-	
t_f	Turn-off Fall Time		-	22	-	
Gate Charge Characteristics[b]						
Q_g	Total Gate Charge	V_{DS} = 100 V, V_{GS} = 10 V, I_{DS} = 30 A	-	30		nC
Q_{gs}	Gate-Source Charge		-	14		
Q_{gd}	Gate-Drain Charge		-	7		

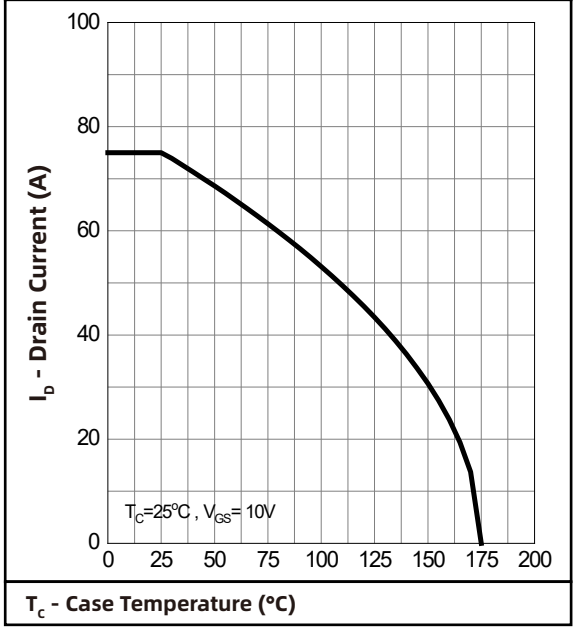
Notes :
a : Pulse test ; pulse width ≤ 300 μs, duty cycle ≤ 2%
b : Guaranteed by design, not subject to production testing

7. Typical Characteristics

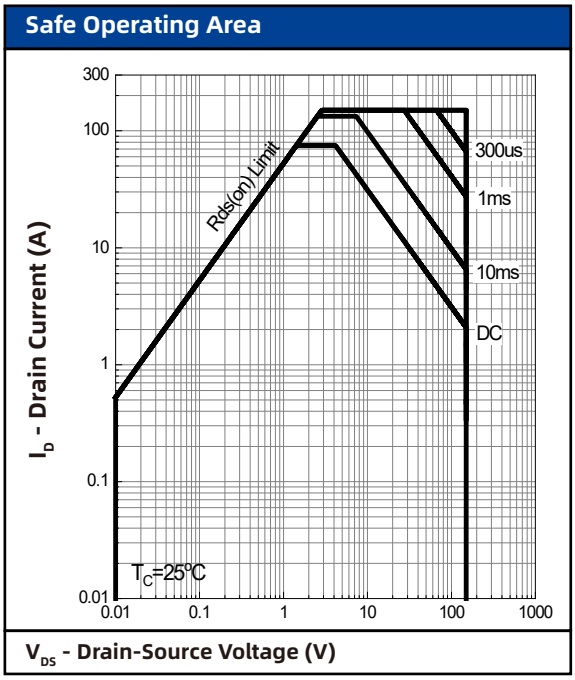
Power Capability



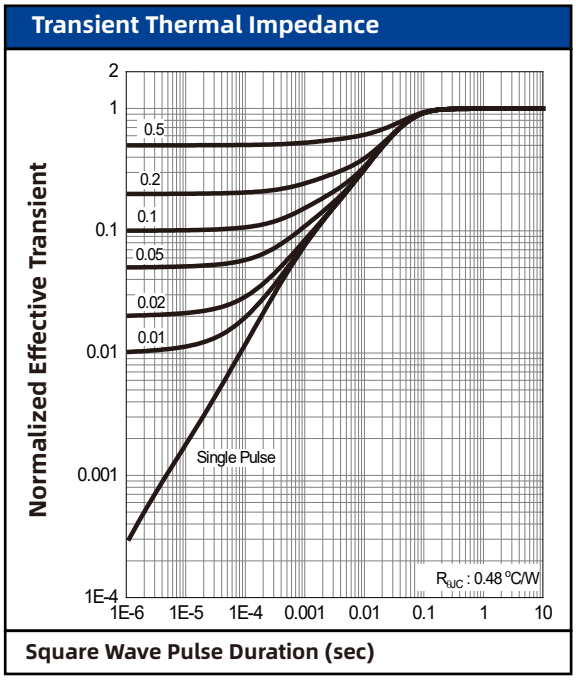
Current Capability



Safe Operating Area

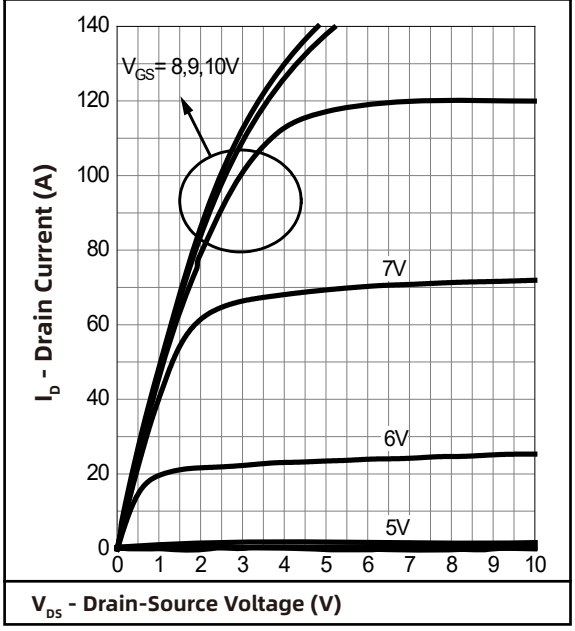


Transient Thermal Impedance

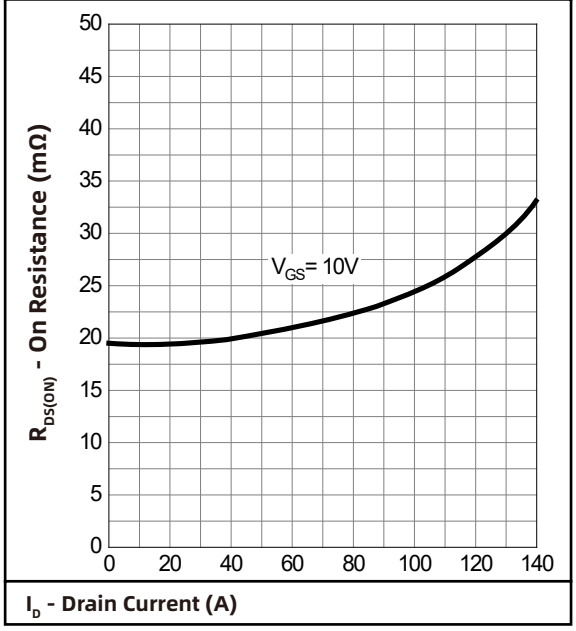


7. Typical Characteristics (cont.)

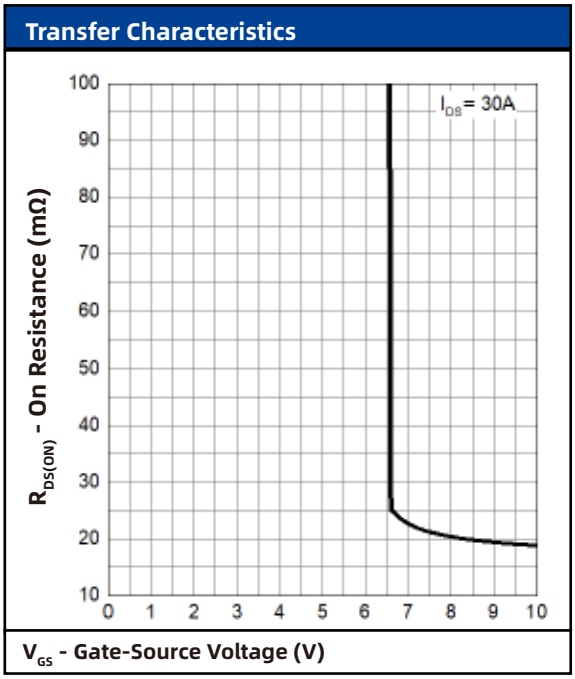
Output Characteristics



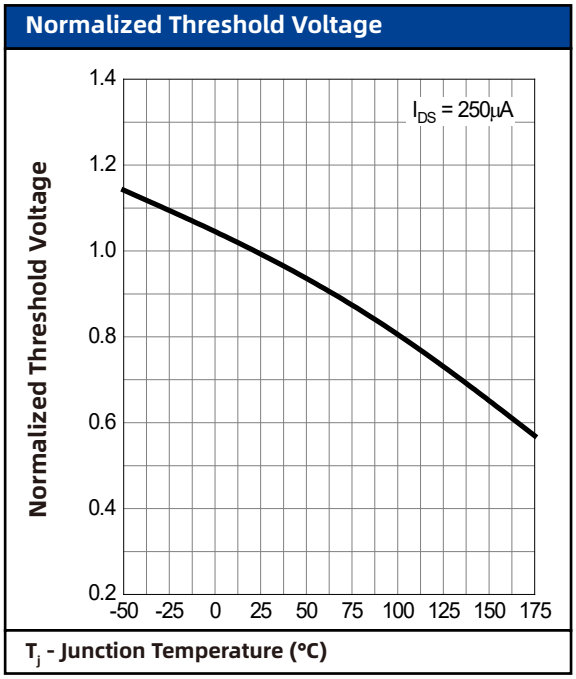
On Resistance



Transfer Characteristics

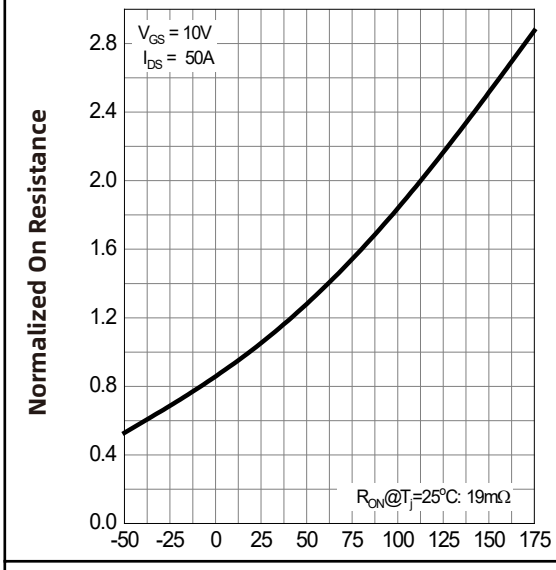


Normalized Threshold Voltage

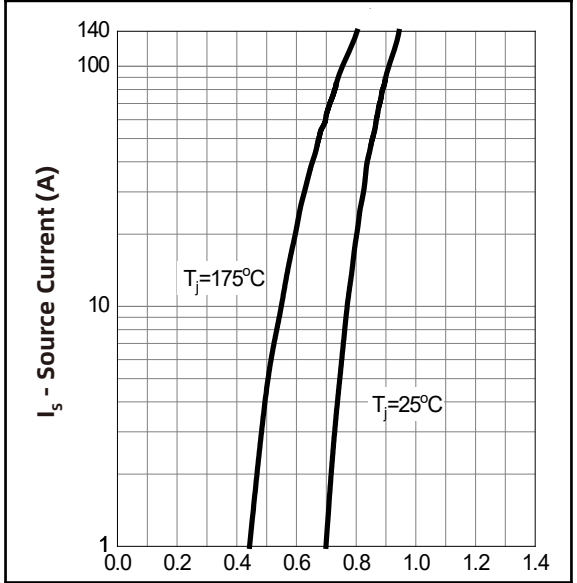


7. Typical Characteristics (cont.)

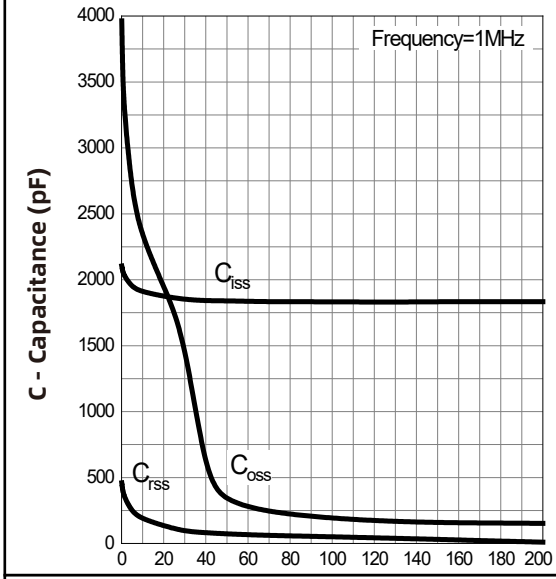
Normalized On Resistance



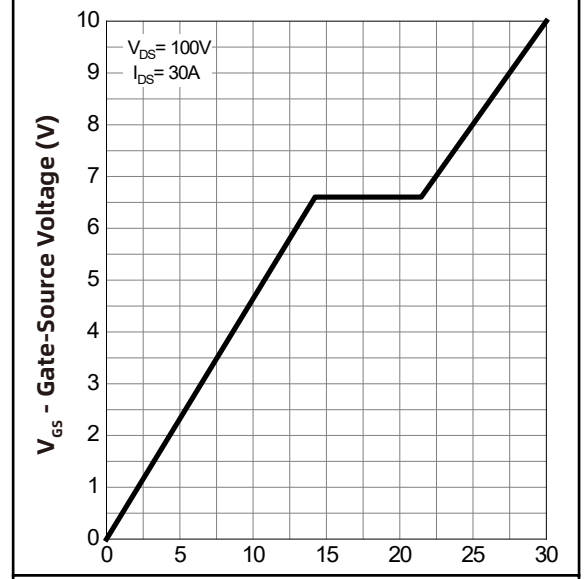
Diode Forward Current



Capacitance

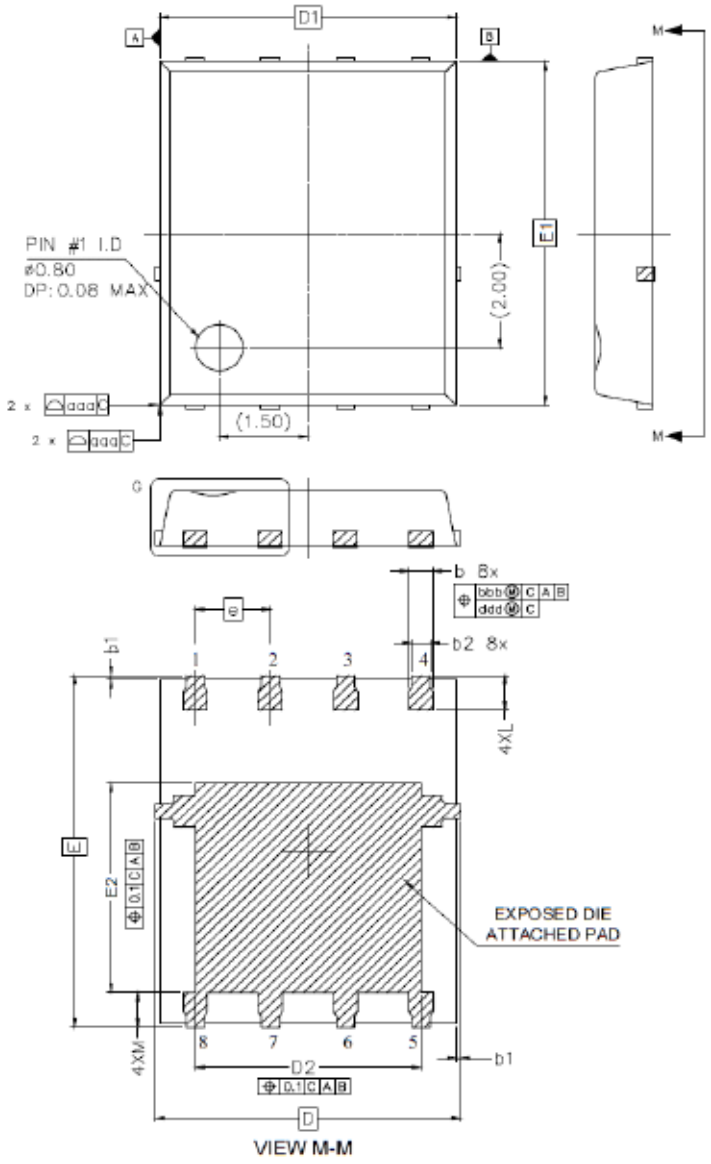


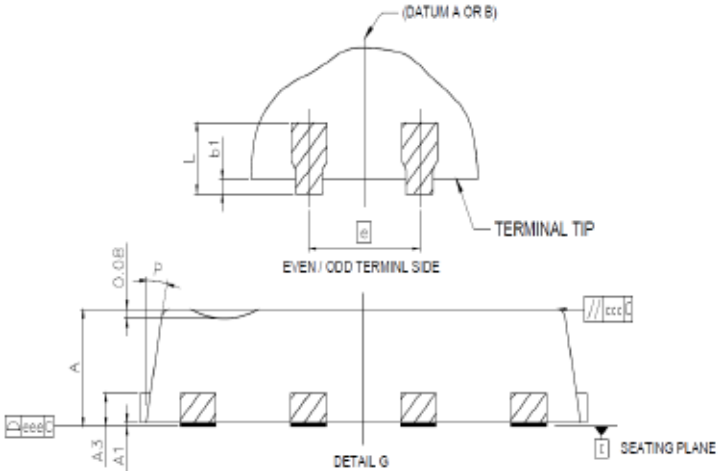
Gate Charge



8. Package Dimensions

PDFN5*6-8L Package





Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.95	1.05
A1	0.00	0.05
A3	0.254REF	
b	0.31	0.51
b1	0.03	0.13
b2	0.21	0.41
D	5.15BSC	
D1	5.00BSC	
D2	3.70	3.90
E	6.15BSC	
E1	6.00BSC	
E2	3.56	3.76
e	1.27BSC	
L	0.51	0.71
M	0.51	0.71
p	10°	12°
aaa	0.10	
bbb	0.10	
ccc	0.10	
ddd	0.05	
eee	0.08	